

IN THE CLAIMS:

Please amend claim 1 as follows:

1 1. (Once Amended) [1.] A trench transistor comprising:
2 a substrate having a surface;
3 a trench extending a selected depth into the substrate from the surface, the
4 trench having a sidewall;
5 a gate structure at least partially within the trench; and
6 a source region self aligned to the gate structure.

REMARKS

Upon entry of this amendment, which amends claim 1, claims 1-10 remain pending. The drawings were objected to under M.P.E.P. § 818.03(a). Previously examined claim 1 was rejected under 35 U.S.C. § 112, Second Paragraph; claims 1-6 and 8 were rejected under 35 U.S.C. § 102(e) as being anticipated by U.S. Patent No. 5,970,344 to Kubo et al. (hereinafter "Kubo"); claim 7 was rejected under 35 U.S.C. § 103(a) as being unpatentable over Kubo; and claims 9-10 were rejected under 35 U.S.C. § 103(a) as being unpatentable over Kubo in view of admitted prior art. Applicant respectfully requests reconsideration of the claims in view of the above amendments and the comments below.

Objections to the Drawings

The drawings (specifically Figures 1-3) were objected to under M.P.E.P. § 818.03(a) for not providing a legend indicated that these figures referred to prior art. In response, Applicant has filed, in a separate paper as required by 37 C.F.R. 1.21(a)(3)(ii), proposed changes to the drawings, the proposed changes presented in red ink. Applicant respectfully requests that the Examiner approve the proposed changes.